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Docket No.

211897US99

IN THE UNFFED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Robert J. HIGGINS, et al.

SERIAL NO:

D: 09/911,496

GAU:

2814

FILED:

July 25, 2001

EXAMINER: WILLE

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FOR:

MONOLITHIC SEMICONDUCTOR-PIEZOELECTRIC DEVICE STRUCTURES AND ELECTRO-ACOUSTIC CHARGE TRANSPORT DEVICES

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR ±197

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- □ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number <u>15-0030</u>. A duplicate copy of this sheet is enclosed.

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Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEWSTADT, P.C.

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U.S. DEPARTMENT OF COMMENCE ATTY DOCKET NO. SERIAL NO. Form PTO 1449 (Modified) PATENT AND TRADEMARK OFFICE 211897US99 09/911,496 **APPLICANT** LIST OF REFERENCES CITED BY APPLICANT Robert J. HIGGINS, et al. **FILING DATE GROUP** July 25, 2001 2814 **U.S. PATENT DOCUMENTS EXAMINER** DOCUMENT SUB FILING DATE DATE **CLASS** NAME INITIAL NUMBER **CLASS** IF APPROPRIATE ΧN 6,233,435 B1 05/15/01 WONG XO 4,723,321 02/02/88 SALEH ΧP 6,181,920 B1 01/30/01 **DENT ET AL** XQ 6,415,140 B1 07/02/02 BENJAMIN ET AL XR 5,760,740 06/02/98 **BLODGETT** XS 5,238,877 08/24/93 **RUSSELL** XT 4,876,218 10/24/89 **PESSA ET AL** m > XU 6,232,242 B1 05/15/01 HATA ET AL XV 4,378,259 03/29/83 HASEGAWA ET AL 6 XW 6,278,541 B1 08/21/01 BAKER 3 XY 4,298,247 11/03/81 MICHELET ET AL ΧZ 4,174,504 11/13/79 CHENAUSKY ET AL YA 3,758,199 09/11/73 **THAXTER** YB 6,362,558 B1 03/26/02 **FUKUI** YC 6,140,746 10/31/00 MIYASHITA ET AL YD 2002/0076878 A1 06/20/02 WASA ET AL ΥE 6,419,849 B1 07/16/02 QIU ET AL YF 2002/0179000 A1 12/05/02 LEE ET AL YG 6,341,851 01/29/02 TAKAYAMA ET AL YΗ 2001/0055820 A1 12/27/01 SAKURAI ET AL ΥI 6,204,525 B1 03/20/01 SAKURAI ET AL ΥJ 5,985,404 11/16/99 YANO ET AL ΥK 6,538,359 B1 03/25/03 HIRAKU ET AL YL 6,498,358 B1 12/24/02 LACH ET AL ΥM 02/07/95 5,387,811 SAIGOH ΥN 5,523,602 06/04/96 HORIUCHI ET AL YO 5,362,998 11/08/94 **IWAMURA ET AL** ΥP 5,188,976 02/23/93 KUME ET AL Examiner **Date Considered**

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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

ATTY DOCKET NO. SERIAL NO. U.S. DEPARAMENT OF COMMERCE Form PTO 1449 (Modified) 211897US99 09/911,496 **APPLICANT** \overline{c} LIST OF REFERENCES CITED BY APPLICANT Robert J. HIGGINS, et al. **FILING DATE GROUP** 2814 July 25, 2001 **U.S. PATENT DOCUMENTS** FILING DATE **EXAMINER DOCUMENT** SUB DATE NAME **CLASS** IF APPROPRIATE INITIAL CLASS NUMBER YQ 6,501,121 B1 12/31/02 YU ET AL YR 5,919,515 07/06/99 YANO ET AL 08/24/93 RUSSELL YS 5,238,877 ΥT **DENNARD ET AL** 5,540,785 07/30/96 YU 5,997,638 12/07/99 **COPEL ET AL** YV 6,291,866 09/18/01 **WALLACE** COOPER, JR ET AL YW 11/15/94 5,365,477 ΥX 5,548,141 08/20/96 MORRIS ET AL YY 2002/0021855 02/21/02 KIM Yυ ΥZ 6,110,840 08/29/00 ZΑ 09/16/97 5,667,586 **EK ET AL** ΖB 5,313,058 05/17/94 FRIEDERICH ET AL ZC 5,315,128 05/24/94 **HUNT ET AL BAUM ET AL** ZD 07/06/99 5,919,522 ZΕ 4,843,609 06/27/89 OHYA ET AL ZF 12/02/86 **KUWANO ET AL** 4,626,878 4,525,871 ZG 06/25/85 **FOYT ET AL** ZH 3,818,451 06/18/74 **COLEMAN** ZΙ 6,059,895 05/09/00 **CHU ET AL** ΖJ 4,447,116 05/08/84 KING ET AL ΖK 02/08/00 **BINKLEY ET AL** 6,022,671 ZL 05/19/98 SUZUKI ET AL 5,754,714 ZΜ 6,524,651 B2 02/25/03 **GAN ET AL** ZN 6,355,945 B1 03/12/03 KADOTA ET AL 06/24/97 **TOHYAMA ET AL** ZO 5,642,371 ZΡ 09/03/02 **ABELES** 6,445,724 B2 ZQ 5,753,934 05/19/98 YANO ET AL ZR 6,326,667 B1 12/04/01 SUGIYAMA ET AL ZS 04/18/00 **MASUDA** 6,051,874 ZΤ 5,166,761 11/24/92 **OLSON ET AL**

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